SLRS020A - DECEMBER 1978 - REVISED NOVEMBER 1995

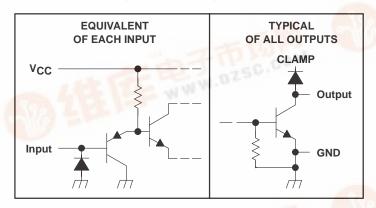
- Very Low Power Requirements
- Very Low Input Current
- Characterized for Use to 350 mA
- No Output Latch-Up at 50 V (After Conducting 300 mA)
- High-Voltage Outputs (70 V Min)
- Output Clamp Diodes for Transient Suppression (350 mA, 70 V)
- TTL- or MOS-Compatible Diode-Clamped Inputs
- Standard Supply Voltage
- Suitable for Hammer-Driver Applications

description

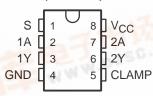
The SN75446 and SN75447 dual peripheral drivers are designed for use in systems that require high current, high voltage, and fast switching times. The SN75446 and SN75447 provide AND and NAND drivers, respectively. These devices have diode-clamped inputs as well as high-current, high-voltage inductive-clamp diodes on the outputs.

The SN75446 and SN75447 drivers are characterized for operation from 0°C to 70°C.

schematics of inputs and outputs



D OR P PACKAGE (TOP VIEW)



Function Tables

SN75446 (each AND driver)

INPU	OUTPUT			
Α	S	Υ		
Н	Н	Н		
L	X	11/1		
X	L	L.C.		

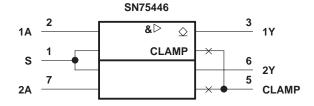
SN75447 (each NAND driver)

INPU	OUTPUT			
Α	S	Y		
Н	Н	L		
L	X	Н		
Х	L	Н		

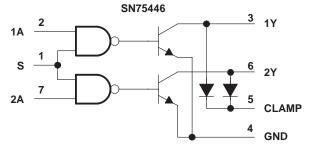
H = high level, L = low level

X = irrelevant

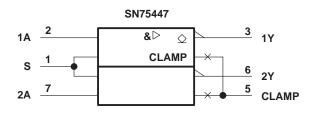
logic symbols†

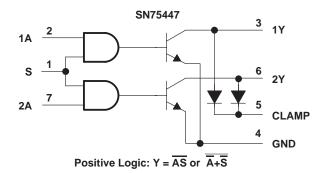


logic diagrams (positive logic)



Positive Logic: $Y = \overline{AS}$ or $\overline{A+S}$





[†] This symbol is in accordance with ANSI/IEEE Std 91-1984 and IEC publication 617-12.

absolute maximum ratings over operating free-air temperature range (unless otherwise noted)‡

Supply voltage, V _{CC} (see Note 1)	
Input voltage, V _I	
Output current, IO (see Note 2)	400 mA
Output clamp-diode current	400 mA
Continuous total power dissipation	See Dissipation Rating Table
Operating free-air temperature range, T _A	0°C to 70°C
Storage temperature range, T _{Stq}	65°C to 150°C
Lead temperature 1,6 mm (1/16 inch) from case for 10 seconds	260°C

[‡] Stresses beyond those listed under "absolute maximum ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated under "recommended operating conditions" is not implied. Exposure to absolute-maximum-rated conditions for extended periods may affect device reliability.

NOTES: 1. Voltage values are with respect to network GND.

2. Both halves of this dual circuit may conduct rated current simultaneously; however, power dissipation averaged over a short time interval must fall within the continuous dissipation ratings.

DISSIPATION RATING TABLE

PACKAGE	$T_{\mbox{A}} \le 25^{\circ}\mbox{C}$ POWER RATING	DERATING FACTOR ABOVE T _A = 25°C	T _A = 70°C POWER RATING
D	725 mW	5.8 mW/°C	464 mW
Р	1000 mW	8.0 mW/°C	640 mW



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recommended operating conditions

	MIN	NOM	MAX	UNIT
Supply voltage, V _{CC}	4.75	5	5.25	V
High-level input voltage, VIH	2			V
Low-level input voltage, V _I L			0.8	V
Operating free-air temperature range, T _A	0		70	°C

electrical characteristics over recommended operating free-air temperature range

PARAMETER			TEST C	TEST CONDITIONS		TYP [†]	MAX	UNIT
VIK	Input clamp voltage		$I_{I} = -12 \text{ mA}$	I _I = -12 mA		-0.9	-1.5	V
	Law law law taut with the			I _{OL} = 100 mA		0.1	0.3	
\/ - .			$V_{CC} = 4.75 \text{ V},$	I _{OL} = 200 mA		0.22	0.45	
VOL	Low-level output voltage	-level output voltage	V _{IH} = 2 V, V _{IL} = 0.8 V	I _{OL} = 300 mA		0.45	0.65	V
				I _{OL} = 350 mA		0.55	0.75	
V _{O(BR)}	Output breakdown voltage		$V_{CC} = 4.75 \text{ V},$	I _{OH} = 100 μA	70	100		V
V _{R(K)}	Output clamp-diode reverse voltage		V _{CC} = 4.75 V,	I _R = 100 μA	70	100		V
V _F (K)	Output clamp-diode forward voltage		V _{CC} = 4.75 V,	I _F = 350 mA	0.6	1.2	1.6	V
ЮН	High-level output current		V _{CC} = 4.75 V, V _{IL} = 0.8 V,	V _{IH} = 2 V, V _{OH} = 70 V		1	100	μΑ
lн	High-level input current		V _{CC} = 5.25 V,	V _I = 5.25 V		0.01	10	μА
L	Low lovel input gurrent	A input	V 505 V	V- 0.0 V		-0.5	-10	
'IL	Low-level input current	S input	$V_{CC} = 5.25 \text{ V},$	$V_{ } = 0.8 V$		-1	-20	μΑ
1	Complete summer to extend to bigh	SN75446	V 505 V	V _I = 5 V		11	1 18	A
ICCH	Supply current, outputs high	SN75447	V _{CC} = 5.25 V	V _I = 0		11	18	mA
	Supply current, outputs low	SN75446	V	V _I = 0		11	18	A
ICCL		SN75447	V _{CC} = 5.25 V	V _I = 5 V		11	18	mA

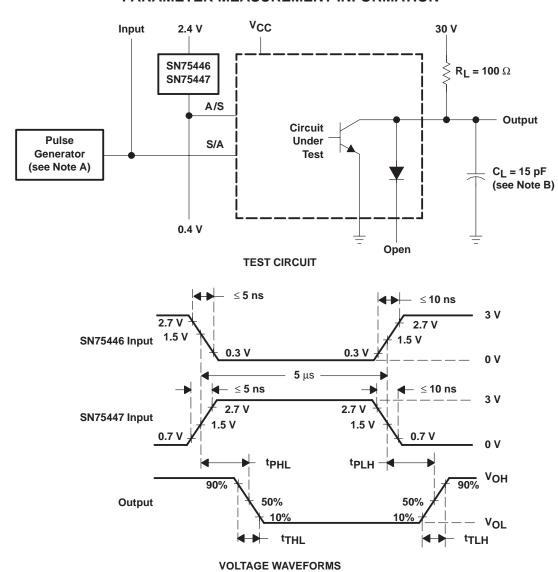
 $[\]dagger$ All typical values are at V_{CC} = 5 V, T_A = 25°C.

switching characteristics, V_{CC} = 5 V, T_A = 25°C

PARAMETER		TEST CONDITIONS		MIN	TYP	MAX	UNIT
tPLH	Propagation delay time, low-to-high-level output				300	750	ns
tPHL	Propagation delay time, high-to-low-level output	C_L = 15 pF, R_L = 100 Ω , See Figure 1			200	500	ns
tTLH	Transition time, low-to-high-level output				50	100	ns
tTHL	Transition time, high-to-low-level output				50	100	ns
Vон	High-level output voltage after switching	V _S = 55 V, See Figure 2	$I_O \approx 300 \text{ mA},$	V _S -0.018		·	٧



PARAMETER MEASUREMENT INFORMATION



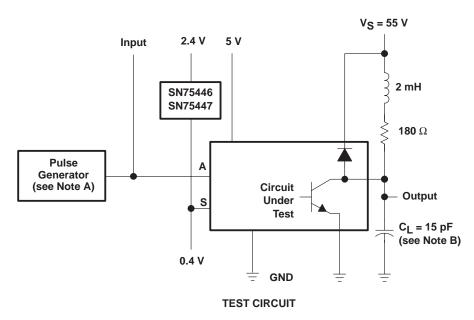
NOTES: A. The pulse generator has the following characteristics: PRR = 100 kHz, Z_O = 50 Ω .

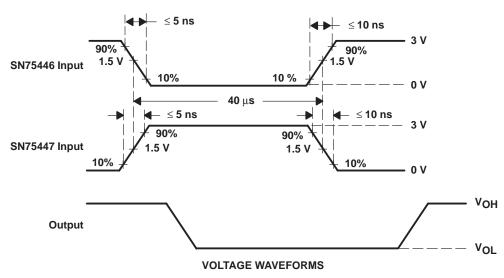
B. C_L includes probe and jig capacitance.

Figure 1. Test Circuit and Voltage Waveforms, Switching Characteristics



PARAMETER MEASUREMENT INFORMATION





NOTES: A. The pulse generator has the following characteristics: PRR = 12.5 kHz, Z_O = 50 Ω .

B. C_L includes probe and jig capacitance.

Figure 2. Latch-Up Test Circuit and Voltage Waveforms



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